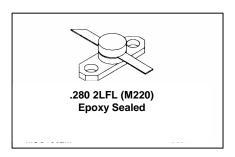


### **MS2205**

# RF & MICROWAVE TRANSISTORS AVIONICS APPLICATIONS

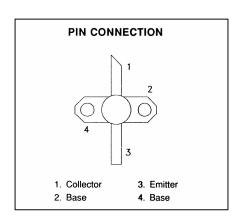
#### **Features**

- 1025-1150 MHz
- GOLD METALLIZATION
- INFINITE VSWR CAPABILITY @ RATED CONDITIONS
- Pout = 4 W MINIMUM
- G<sub>P</sub>= 10 dB
- COMMON BASE CONFIGURATION



### **DESCRIPTION:**

The MS2205 is a common base, silicon NPN microwave transistor designed for Class C driver applications under DME or IFF pulse conditions. This device is capable of withstanding an infinite load VSWR at any phase angle under rated conditions.



### ABSOLUTE MAXIMUM RATINGS (Tcase = 25°C)

Symbol	Parameter	Value	Unit
P <sub>DISS</sub>	Power Dissipation	7.5	W
V <sub>CE</sub>	Collector-Emitter Bias Voltage	37	V
TJ	Junction Temperature	200	o <b>c</b>
Ic	Device Current	1.0	Α
T <sub>STG</sub>	Storage Temperature	-65 to +200	o <b>c</b>

#### Thermal Data

R <sub>TH(J-C)</sub>	Junction-case Thermal Resistance*	35	°C/W

Revision 1



### MS2205

## ELECTRICAL SPECIFICATIONS (Tcase = 25°C)

### **STATIC**

Symbol	Test Conditions			Value		
			Min.	Typ.	Max.	Unit
BV <sub>CBO</sub>	I <sub>C</sub> = 1 mA	I <sub>E</sub> = 0 mA	45			V
BV <sub>CEO</sub>	$I_C = 5 \text{ mA}$	I <sub>B</sub> = 0mA	20			V
BV <sub>EBO</sub>	I <sub>E</sub> = 1.0 mA	I <sub>C</sub> = 0 mA	3.5			V
I <sub>CES</sub>	V <sub>CE</sub> = 35 V				1.0	mA
HFE	V <sub>CE</sub> = 5 V	I <sub>C</sub> = 100 mA	20		120	

### **DYNAMIC**

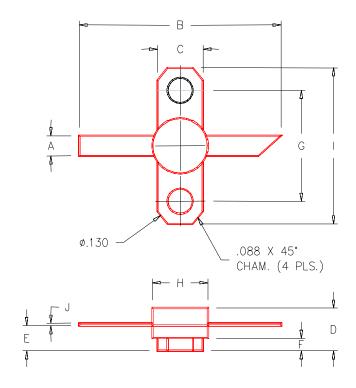
Symbol	Test Conditions		Value		
		Min.	Typ.	Max.	Unit
P <sub>OUT</sub>	f =1025 - 1150 MHz P <sub>IN</sub> = 400mW V <sub>CE</sub> =35V	4			W
G <sub>P</sub>	f =1025 - 1150 MHz P <sub>IN</sub> = 400mW V <sub>CE</sub> =35V	10			dB
Conditions	Pulse Width = 10 μs Duty Cycle = 1%				





### **PACKAGE MECHANICAL DATA**

#### PACKAGE STYLE M220



	MINIMUM	MAXIMUM	П		MINIMUM	MAXIMUM
	INCHES/MM	INCHES/MM			INCHES/MM	INCHES/MM
Α	.100/2,54			J	.003/0,08	.006/0,15
В	1.050/26,67		П			
С	.250/6,35					
D		.210/5,33				
Е	.120/3,05	.130/3,30				
F	.062/1,58					
G	.562/	14,28				
Н		.285/7,24				
1	.800/20,32					